

Notice of References Cited	Application/Control No. 09/997,396		Applicant(s)/Patent Under Reexamination HUJANEN ET AL.	
	Examiner DAVID VU		Art Unit 2818	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-6,144,060	11-2000	Park et al.	257/310
*	C	US-6,478,931	11-2002	Wadley et al.	204/192.12
*	D	US-5,780,175	07-1998	Chen et al.	428/692
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	M. Utriainen et al., Studies of metallic thin film growth in an atomic layer epitaxy reactor using M (acac) ₂ (M= Ni, Cu, Pt) precursors) (Applied Surface Science 157 (2000) 151-158.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.